

Bipolar Transistor

-100 V, -2.5 A, Low $V_{\text{CE(sat)}}$ PNP Single LFPAK

NSS1001CL

This device is bipolar junction transistor featuring high current, low saturation voltage, and high speed switching.

Suitable for automotive applications. AEC-Q101 qualified and PPAP capable. (NSVS1001CLTWG)

Features

- Complement to NSS1002CL
- Large Current Capacitance
- Low Collector to Emitter Saturation Voltage
- Thin Profile LFPAK8 3.3 x 3.3 Package
- High-Speed Switching
- High Allowable Power Dissipation
- AEC-Q101 Qualified and PPAP Capable (NSVS1001CLTWG)
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Load Switch
- Gate Driver Buffer
- DC-DC Converters

Specifications

ABSOLUTE MAXIMUM RATING at Ta = 25°C

Parameter	Symbol	Value	Unit
Collector-to-Base Voltage	V _{CBO}	-120	V
Collector-to-Emitter Voltage	V _{CEO}	-100	V
Emitter-to-Base Voltage	V _{EBO}	-7	V
Collector Current	I _C	-2.5	Α
Collector Current (Pulse)	I _{CP}	-4	Α
Collector Dissipation	P _C (Note 1)	0.8	W
	P _C (Note 2)	2.2	
Junction Temperature	TJ	175	°C
Storage Temperature Range	T _{stg}	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

- Mounted on FRB with minimum pad of Copper 2 oz
- 2. Mounted on FRB with 1 in/sq pad of Copper 2 oz



LFPAK8 3.3x3.3, 0.65P CASE 760AD

ELECTRICAL CONNECTION



MARKING DIAGRAM

NSS 1001G AWLYW

NSS1001 = Specific Device Code

A = Assembly Location

WL = Wafer Lot
Y = Year
W = Work Week
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS at Ta = 25°C

			Value			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I _{CBO}	VCB = -120 V IE = 0 A			-0.1	μΑ
Emitter Cutoff Current	I _{EBO}	VEB = -7 V IC = 0 A			-0.1	μΑ
DC Current Gain	h _{FE}	VCE = -5 V IC = -100 mA	140		400	
Gain-Bandwidth Product	f _T	VCE = -10 V IC = -100 mA		200		MHz
Output Capacitance	C _{ob}	VCB = -10 V f = 1 MHz		24		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)1}	IC = -100 mA IB = -10 mA		-0.025	-0.05	V
	V _{CE(sat)2}	IC = -1 A IB = -100 mA		-0.08	-0.16	V
	V _{CE(sat)3}	IC = -2.5 A IB = -250 mA		-0.3	-0.6	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	IC = -1 A IB = -100 mA		-0.85	-1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	IC = -10 μA, IE = 0 A	-120			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	IC = −1 mA, RBE = ∞	-100			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	IE = -10 μA, IC = 0 A	-7			V
Turn-On Time	t _{on}	See Figure 1		24		ns
Storage Time	t _{stg}			440		ns
Fall Time	t _f			20		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

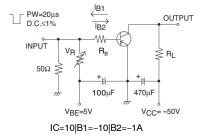


Figure 1. Switching Time Test Circuit

ESD RATING

Parameter	Symbol	Value	Unit	Class
Electrostatic Discharge – Human Body Model	НВМ	>2000, <4000	V	2
Electrostatic Discharge – Machine Model	MM	>400	V	M4

TYPICAL CHARACTERISTICS

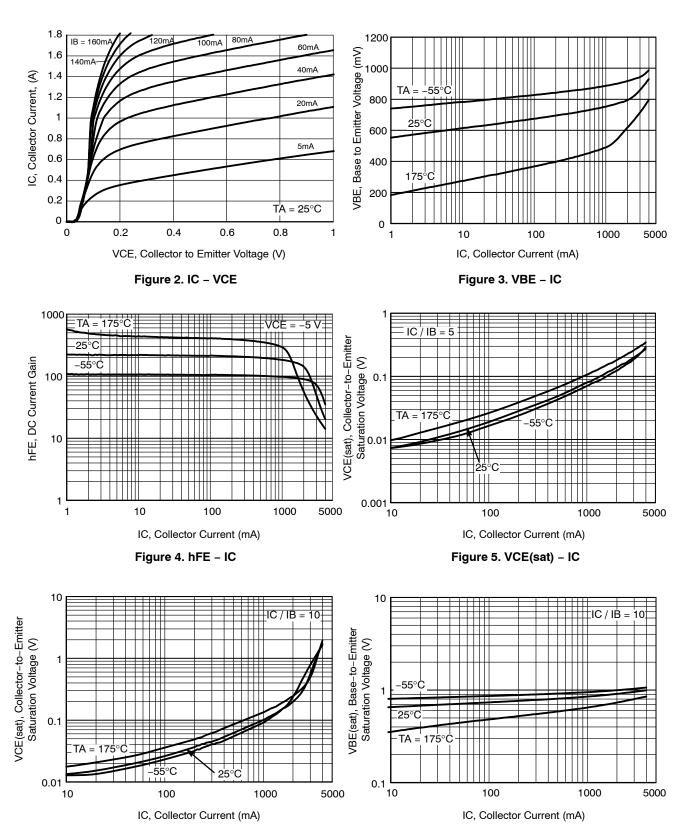


Figure 6. VCE(sat) - IC

Figure 7. VBE(sat) - IC

TYPICAL CHARACTERISTICS

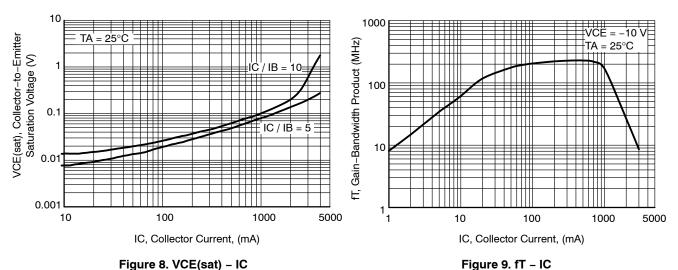


Figure 8. VCE(sat) - IC

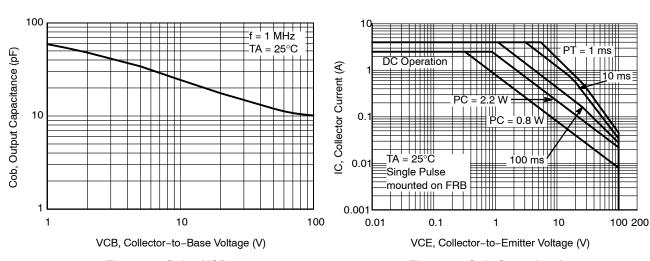


Figure 10. Cob - VCB

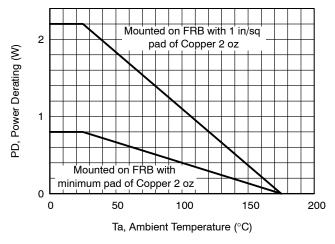


Figure 12. Power Derating

Figure 11. Safe Operating Area

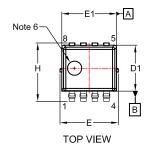
ORDERING INFORMATION

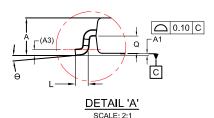
Device	Marking	Package	Shipping (Qty / Packing) [†]
NSVS1001CLTWG	NSS1001G	LFPAK8 (Pb-Free / Halogen Free)	3,000 / Tape & Reel
NSS1001CLTWG	NSS1001G	LFPAK8 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

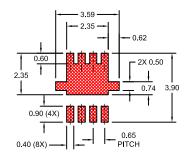
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D









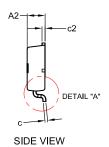


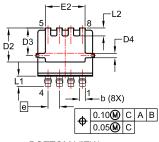
LAND PATTERN RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

LFPAK8 3.3x3.3, 0.65P CASE 760AD

ISSUE E **DATE 16 NOV 2020**





BOTTOM VIEW

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS, MOLD FLASH, PROTRUSIONS OR BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
- 4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- DATUMS A AND B ARE DETERMINED AT DATUM PLANE H
- OPTIONAL MOLD FEATURE.

DIM	MILLIMETERS			
5	MIN.	NOM.	MAX.	
Α	0.95	1.05	1.15	
A1	0.00	0.05	0.10	
A2	0.95	1.00	1.05	
А3		0.15 RE	F	
q	0.27	0.32	0.37	
С	0.12	0.17	0.22	
c2	0.12	0.17	0.22	
D1	2.50	2.60	2.70	
D2	1.82	1.92	2.02	
D3	1.46	1.56	1.66	
D4	0.20	0.25	0.30	
Е	3.20	3.30	3.40	
E1	3.00	3.10	3.20	
E2	2.15	2.25	2.35	
е	0.65 BSC			
I	3.20	3.30	3.40	
L	0.25	0.37	0.50	
L1	0.48	0.58	0.68	
L2	0.35	0.45	0.55	
Q	0.45	0.50	0.55	
θ	0°	4°	8°	

GENERIC MARKING DIAGRAM*

XXXXX XXXXX **AWLYW**

XXXX = Specific Device Code = Assembly Location

WL = Wafer Lot = Year W = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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For additional information, please contact your local Sales Representative at

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